

DATA SHEET

MOS FIELD EFFECT TRANSISTOR $\mu PA1741TP$

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

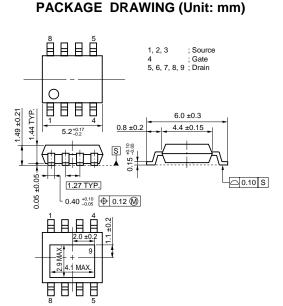
The μ PA1741TP is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter.

FEATURES

- High voltage: VDSS = 250 V
- Gate voltage rating: ±30 V
- Low on-state resistance $R_{DS(on)} = 0.79 \ \Omega \text{ MAX.}$ (VGs = 10 V, ID = 2.5 A)
- Low input capacitance
 Ciss = 340 pF TYP. (VDS = 10 V, VGS = 0 V)
- Built-in gate protection diode
- Small and surface mount package (Power HSOP8)

ORDERING INFORMATION

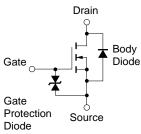
PART NUMBER	PACKAGE				
μΡΑ1741TP	Power HSOP8				



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise noted. All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	250	V	
Gate to Source Voltage (Vps = 0 V)	Vgss	±30	V	EQUIVA
Drain Current (DC) (Tc = 25°C)	D(DC)	±5.0	А	
Drain Current (pulse) ^{Note1}	D(pulse)	±15	А	
Total Power Dissipation (Tc = 25°C)	PT1	21	W	
Total Power Dissipation $(T_A = 25^{\circ}C)^{Note2}$	Рт2	1	W	
Channel Temperature	Tch	150	°C	Gate
Storage Temperature	Tstg	–55 to +150	°C	
Single Avalanche Current Note3	las	5.0	А	Gate
Single Avalanche Energy Note3	Eas	2.5	mJ	Protectior Diode
Repetitive Avalanche Current Note4	AR	5.0	А	
Repetitive Pulse Avalanche Energy Note4	Ear	2.5	mJ	

EQUIVALENT CIRCUIT



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm
- 3. Starting T_{ch} = 25°C, V_{DD} = 125 V, R_G = 25 Ω , L = 100 μ H, V_{GS} = 20 \rightarrow 0 V
- **4.** $T_{ch(peak)} \le 150^{\circ}C, L = 100 \ \mu H$

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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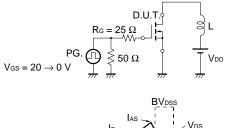
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	Vds = 250 V, Vgs = 0 V			10	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5	3.5	4.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	2	3.5		S
Drain to Source On-state Resistance Note	RDS(on)	Vgs = 10 V, Id = 2.5 A		0.63	0.79	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		340		pF
Output Capacitance	Coss	Vgs = 0 V		70		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		30		pF
Turn-on Delay Time	td(on)	Vdd = 125 V, Id = 2.5 A		11		ns
Rise Time	tr	Vgs = 10 V		8		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		20		ns
Fall Time	tr			6		ns
Total Gate Charge	QG	VDD = 200 V		11		nC
Gate to Source Charge	Q _{GS}	Vgs = 10 V		2		nC
Gate to Drain Charge	Qgd	ID = 5.0 A		5.5		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 5.0 A, VGS = 0 V		0.9	1.5	V
Reverse Recovery Time	trr	IF = 5.0 A, VGS = 0 V		120		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		400		nC

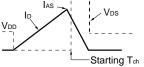
ELECTRICAL CHARACTERISTICS (TA = 25°C, unless otherwise noted. All terminals are conne	cted.)
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Note Pulsed: PW \leq 800 μ s, Duty Cycle \leq 2%

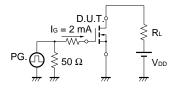
TEST CIRCUIT 1 AVALANCHE CAPABILITY

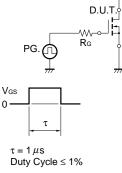
TEST CIRCUIT 2 SWITCHING TIME

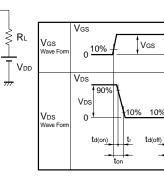




TEST CIRCUIT 3 GATE CHARGE







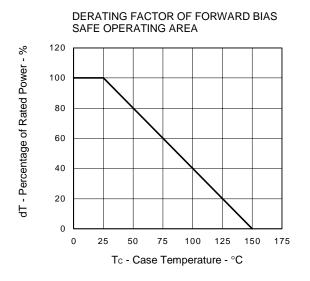
90%

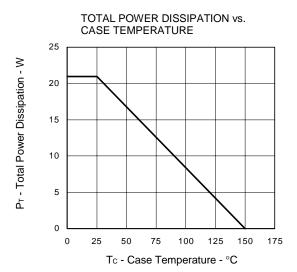
90%

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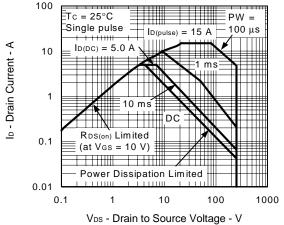
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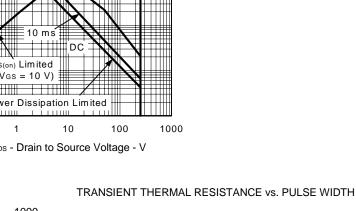
TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

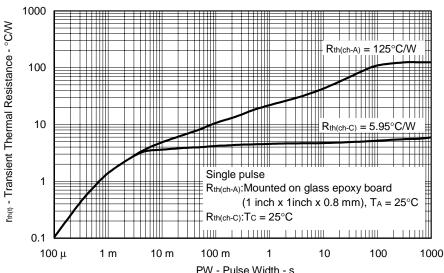




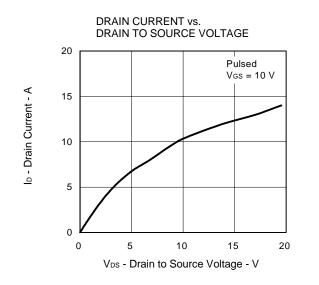
FORWARD BIAS SAFE OPERATING AREA



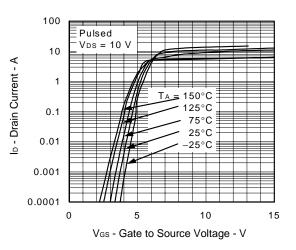




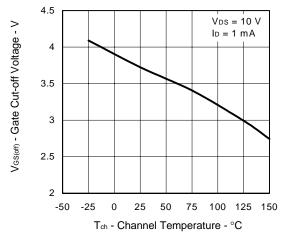
PW - Pulse Width - s



FORWARD TRANSFER CHARACTERISTICS



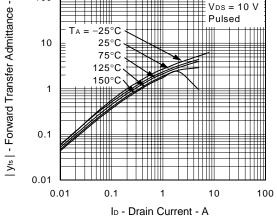
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



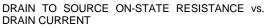
DRAIN CURRENT

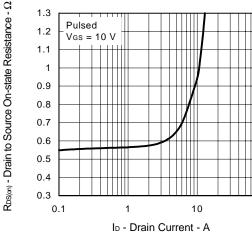
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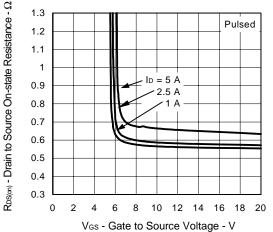


FORWARD TRANSFER ADMITTANCE vs.

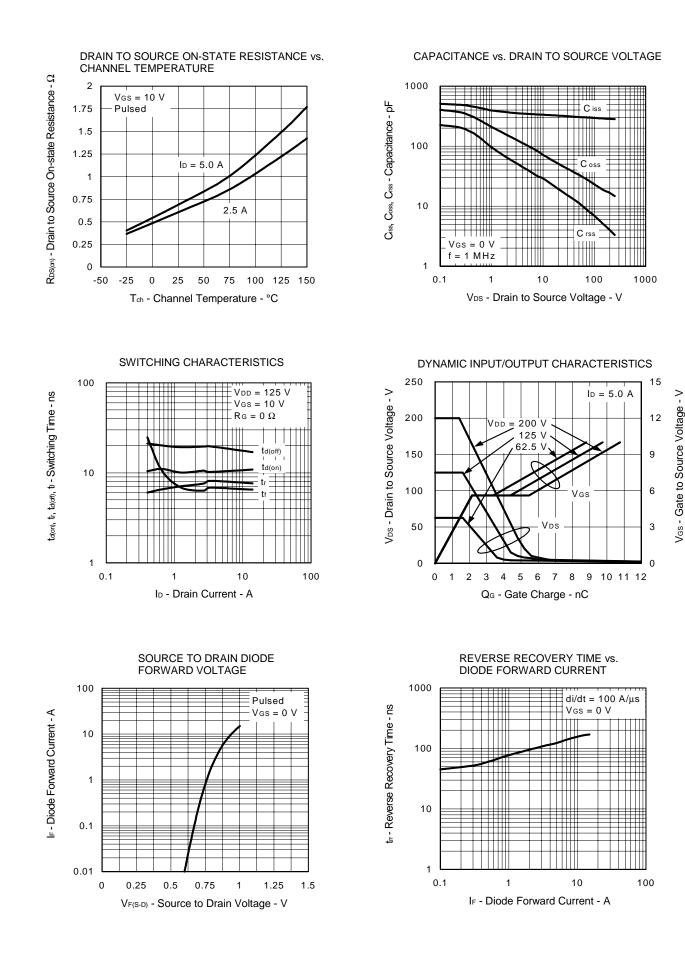




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

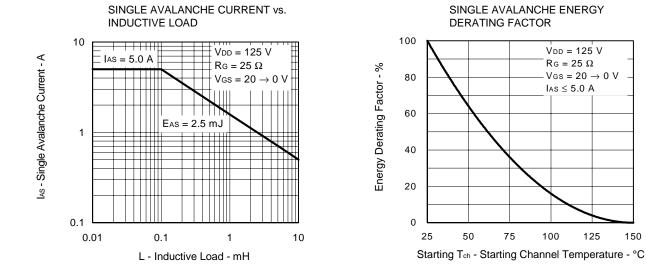


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Data Sheet G16373EJ1V0DS

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